

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	100.00 +/- 0.30 mm	WaferVendor
	2.0	Primary Flat Orientation	<110> +/- 1 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	Wafer Vendor
	5.0	Overall Thickness	353.00 +/- 5.00 um	Guaranteed by Process
	6.0	Total Thickness Variation (TTV)	<3.00um	Guaranteed by Process
	7.0	Bow	<40.00um	Guaranteed by Process
	8.0	Warp	<40.00um	Guaranteed by Process
	9.0	Edge Exclusion	5 mm	Guaranteed by Process
HandleSilicon	10.0	Handle Growth Method	CZ	Wafer Vendor
	11.0	Handle Orientation	<100> +/- 1 degree	Wafer Vendor
	12.0	Handle Thickness	350.00 +/- 5.00 um	Guaranteed by Process
	13.0	Handle Doping Type	P	Wafer Vendor
	14.0	Handle Dopant	Boron	Wafer Vendor
	15.0	Handle Resistivity	1 - 10 Ohmcm	Wafer Vendor
	16.0	Backside Finish	Polished with 1um oxide and lasermark	Nanospec 5pt, 4% sample for oxide thickness
BuriedOxide	16.5	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec 5pt, 4%
	16.6	Oxide Type	Thermal oxidation	Guaranteed by process
	16.7	Oxide formed on	Handle wafer	Guaranteed by process
DeviceSilicon	17.0	Device Growth Method	CZ	epi layer vendor
	18.0	Device Orientation	<100> +/- 1 degree	Wafer Vendor
	19.0	Nominal Thickness	2.00 +/- 0.40 um	Guaranteed by Process, FTIR 9pt 100%
	20.0	Distance to device silicon edge from wafer edge	<= 2mm	Guaranteed by Process
	21.0	Device Doping Type	P	Guaranteed by Process
	22.0	Device Dopant	Boron	Guaranteed by Process
	23.0	Device Resistivity	1 - 10 Ohmcm	Wafer Vendor
	24.0	Voids	none	Guaranteed by Process, SAM inspection
	25.0	Haze	none	Guaranteed by Process, Bright LIght inspection
	26.0	Scratches	none	Guaranteed by Process, Bright LIght inspection
27.0	Device Field Oxidation	5,000.00 +/- 250.00 A	Nanospec 4%, 5pt	
28.0	LPCVD Polysilicon deposition thickness	5,000.00 +/- 1,000.00 A	nanospec 4%, 5pt	

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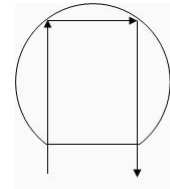
Customer

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DeviceSilicon	29.0 Surface Implant	Species = Boron, Dose = 1.5e15 at/cm ³ , Energy = 80keV, no screen oxide	Into polysilicon - mplant vendor

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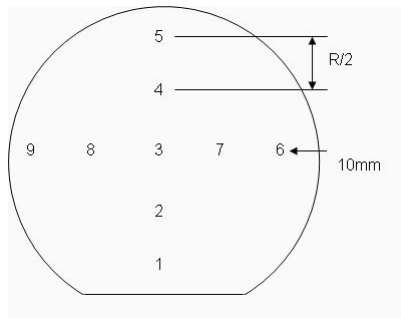
Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information